

# **ISC Silicon NPN Power Transistor**

**AD162** 

### **DESCRIPTION**

- · Wide Area of Safe Operation
- · DC Current Gain-
  - : h<sub>FE</sub>=50-350@I<sub>C</sub>= 0.5A
- Collector-Emitter Saturation Voltage-
  - : V<sub>CE(sat</sub>)= 0.7V(Max)@ I<sub>C</sub>= 3A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

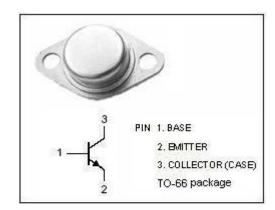
• Designed for general-purpose power switch and amplifier, consumer and industrial applications.

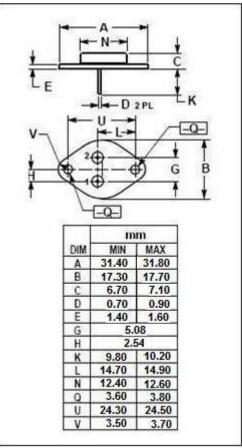
## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	50	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V	
V <sub>EBO</sub>	Emitter-Base Voltage 6		V	
Ic	Collector Current-Continuous	3	Α	
Pc	Collector Power Dissipation @T <sub>C</sub> =25°C	20	W	
TJ	Junction Temperature	150	$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature -55~		$^{\circ}$	

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	8.75	°C/W





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#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA ; I <sub>B</sub> = 0	50		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA ; I <sub>E</sub> = 0	50		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA ; I <sub>C</sub> = 0	6		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.3A		0.7	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.3A		1.2	V
Iceo	Collector Cutoff Current	V <sub>CE</sub> = 50V; I <sub>B</sub> = 0		0.1	mA
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 32V; I <sub>E</sub> = 0		0.5	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6.0V; I <sub>C</sub> =0		10	μА
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 1V	50	350	

### **NOTICE:**

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